

DMN2053U-13 Datasheet



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DiGi Electronics Part Number DMN2053U-13-DG

Manufacturer Diodes Incorporated

Manufacturer Product Number DMN2053U-13

Description MOSFET N-CH 20V 6.5A SOT23 T&R 1

Detailed Description N-Channel 20 V 6.5A (Ta) 800mW (Ta) Surface Mou

nt SOT-23-3



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
DMN2053U-13	Diodes Incorporated
Series:	Product Status:
	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
20 V	6.5A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
1.8V, 10V	29mOhm @ 6A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
1.2V @ 250µA	4.6 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±12V	414 pF @ 10 V
FET Feature:	Power Dissipation (Max):
	800mW (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
SOT-23-3	TO-236-3, SC-59, SOT-23-3
Base Product Number:	
DMN2053	

Environmental & Export classification

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	





N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
001/	$29m\Omega$ @ $V_{GS} = 10V$	6.5A
20V	$35m\Omega @ V_{GS} = 4.5V$	5.4A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- Power Management Functions

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

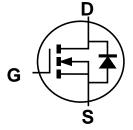
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (§3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

SOT23







Equivalent Circuit

Ordering Information (Notes 4)

Part Number	Case	Packaging
DMN2053U-7	SOT23	3000/Tape & Reel
DMN2053U-13	SOT23	10000/Tape & Reel

D

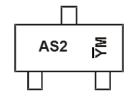
Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

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- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\frac{\text{AS2} = \text{Product Type Marking Code}}{\text{YM} = \text{Date Code Marking}}$ $\frac{\text{Y} = \text{Last Digit of Year (ex: 8 = 2018)}}{\text{M} = \text{Month (ex: 9 = September)}}$

Date Code Key

Year	2017	2018	20	019	2020	2021		2022	2023	20:	24	2025
Code	E	F		G	Н			J	K	L		M
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characte	eristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage		V _{GSS}	±12	V	
Continuous Drain Current (Note 6)	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	6.5 5.4	А
Pulsed Drain Current (380µs Pulse, Du	uty Cycle = 1%)		I _{DM}	22	Α

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P _D	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	160	°C/W	
Total Power Dissipation (Note 6)		PD	1.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	93	°C/W
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	0.95	1.2	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
			26	29		$V_{GS} = 10V, I_D = 6A$
Static Drain-Source On-Resistance	D		28	35		$V_{GS} = 4.5V, I_D = 5A$
Static Diam-Source On-Resistance	R _{DS(ON)}	_	35	48	mΩ	$V_{GS} = 2.5V, I_D = 4A$
			47	91		$V_{GS} = 1.8V, I_D = 2A$
Diode Forward Voltage	V _{SD}	_	0.7	1.0	V	$V_{GS} = 0V$, $I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 8)	•					•
Input Capacitance	C _{iss}	1	414	_	pF	
Output Capacitance	Coss	_	58	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ - f = 1.0MHz
Reverse Transfer Capacitance	C_{rss}	_	43	_	pF	1 - 1.500112
Gate Resistance	R_g	_	3.6	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Q_g	_	4.6	_	nC	45777
Gate-Source Charge	Q_{gs}	_	0.5	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ - In = 6A
Gate-Drain Charge	Q _{gd}	_	1.4	_	nC	- ID = 0A
Turn-On Delay Time	t _{D(ON)}	_	2.6	_	ns	
Turn-On Rise Time	t _R	_	2.9	_	ns	$V_{DD} = 10V, V_{GS} = 5V,$
Turn-Off Delay Time	t _{D(OFF)}	_	13.5	_	ns	$R_L = 1.7\Omega$, $R_G = 6\Omega$
Turn-Off Fall Time	t _F	_	3.8	_	ns	7
Reverse Recovery Time	t _{RR}	_	6.8	_	ns	$I_F = 1.0A$, $di/dt = 100A/\mu s$
Reverse Recovery Charge	Q _{RR}	_	1.2	_	nC	$I_F = 1.0A$, $di/dt = 100A/\mu s$

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing

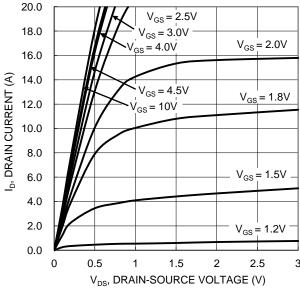


Figure 1. Typical Output Characteristic

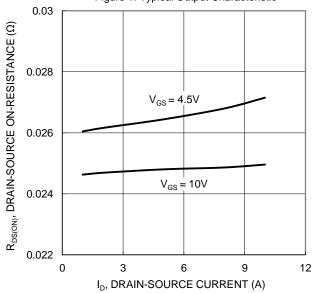


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

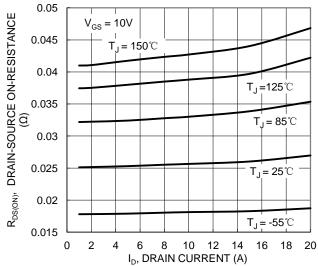


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

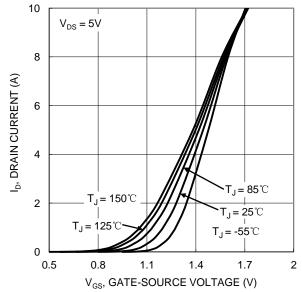


Figure 2. Typical Transfer Characteristic

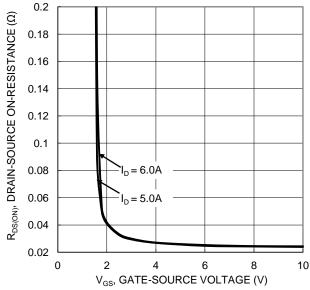


Figure 4. Typical Transfer Characteristic

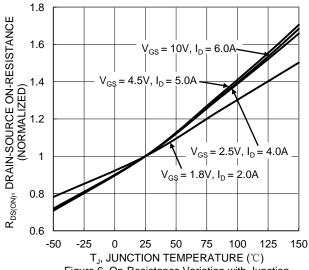


Figure 6. On-Resistance Variation with Junction Temperature



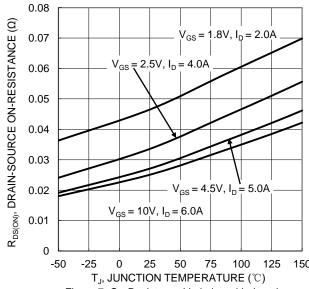


Figure 7. On-Resistance Variation with Junction Temperature

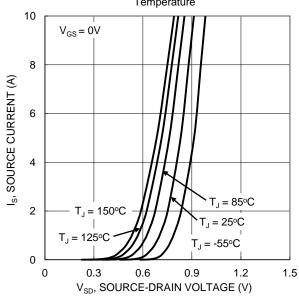
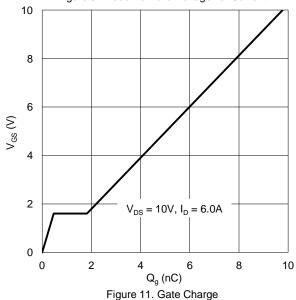


Figure 9. Diode Forward Voltage vs. Current



1.2 $V_{GS(TH)}$, GATE THRESHOLD VOLTAGE (V) 0.9 $I_D = 1mA$ $I_{D} = 250 \mu A$ 0.6 0.3 0 -50 -25 25 50 75 100 125 T_J , JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature

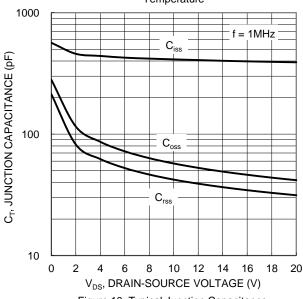
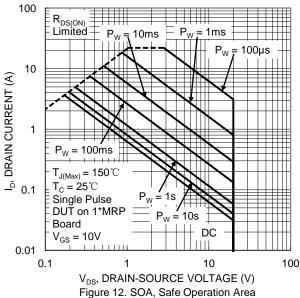


Figure 10. Typical Junction Capacitance



DMN2053U



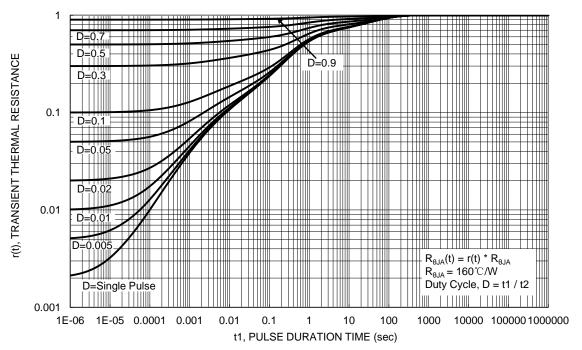


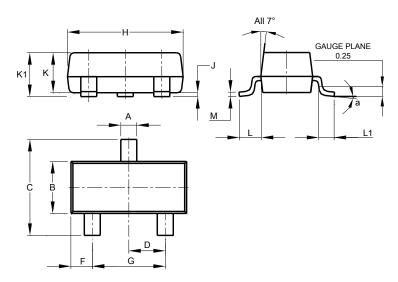
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

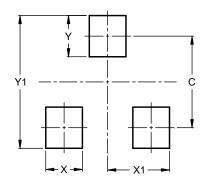


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
M	0.085	0.150	0.110			
а	0°	8°				
All	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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